

Slawomir Kret

List of Publications by Year in descending order

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143
papers

1,944
citations

304368

22
h-index

315357

38
g-index

148
all docs

148
docs citations

148
times ranked

2397
citing authors

#	ARTICLE	IF	CITATIONS
1	The Peak Pairs algorithm for strain mapping from HRTEM images. Ultramicroscopy, 2007, 107, 1186-1193.	0.8	230
2	Extracting Quantitative Information from High Resolution Electron Microscopy. Physica Status Solidi (B): Basic Research, 2001, 227, 247-295.	0.7	111
3	Composition fluctuation in InGaN quantum wells made from molecular beam or metalorganic vapor phase epitaxial layers. Journal of Applied Physics, 2002, 91, 8979-8985.	1.1	92
4	Influence of substrate nitridation temperature on epitaxial alignment of GaN nanowires to Si(111) substrate. Nanotechnology, 2013, 24, 035703.	1.3	74
5	ZnTe nanowires grown on GaAs(100) substrates by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 133114.	1.5	71
6	Catalytic growth of ZnTe nanowires by molecular beam epitaxy: structural studies. Nanotechnology, 2007, 18, 475606.	1.3	55
7	High resolution electron microscope analysis of lattice distortions and In segregation in highly strained In _{0.35} Ga _{0.65} As coherent islands grown on GaAs (001). Journal of Applied Physics, 1999, 86, 1988-1993.	1.1	51
8	GaAs:Mn Nanowires Grown by Molecular Beam Epitaxy of (Ga,Mn)As at MnAs Segregation Conditions. Nano Letters, 2007, 7, 2724-2728.	4.5	47
9	Structural and optical evidence of island correlation in CdTe/ZnTe superlattices. Applied Physics Letters, 2001, 78, 3884-3886.	1.5	42
10	Narrow Excitonic Lines and Large-Scale Homogeneity of Transition-Metal Dichalcogenide Monolayers Grown by Molecular Beam Epitaxy on Hexagonal Boron Nitride. Nano Letters, 2020, 20, 3058-3066.	4.5	35
11	An approach to the systematic distortion correction in aberration-corrected HAADF images. Journal of Microscopy, 2006, 221, 1-7.	0.8	34
12	Giant Spin Splitting in Optically Active ZnMnTe/ZnMgTe Core/Shell Nanowires. Nano Letters, 2012, 12, 3404-3409.	4.5	32
13	All-Wurtzite (In,Ga)As-(Ga,Mn)As Core-Shell Nanowires Grown by Molecular Beam Epitaxy. Nano Letters, 2014, 14, 4263-4272.	4.5	29
14	Elaboration of (111) oriented 3C-SiC/Si layers for template application in nitride epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 9-14.	1.7	28
15	ZnTe-ZnO core-shell radial heterostructures grown by the combination of molecular beam epitaxy and atomic layer deposition. Nanotechnology, 2010, 21, 015302.	1.3	28
16	Natural quantum dots in the InAs-GaAs wetting layer. Applied Physics Letters, 2008, 92, 171104.	1.5	27
17	Enhanced catalyst-free nucleation of GaN nanowires on amorphous Al ₂ O ₃ by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2014, 115, 043517.	1.1	27
18	Growth and characterizations of semipolar (112̂ ²) InN. Journal of Applied Physics, 2012, 112, .	1.1	26

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19	Influence of hydrogen and TMI _n on indium incorporation in MOVPE growth of InGa _N layers. Journal of Crystal Growth, 2014, 402, 330-336.	0.7	26
20	MBE Growth and Properties of ZnTe- and CdTe-Based Nanowires. Journal of the Korean Physical Society, 2008, 53, 3055-3063.	0.3	26
21	Nonlinear FE analysis of residual stresses induced by dislocations in heterostructures. Computational Materials Science, 2004, 29, 379-395.	1.4	25
22	Fine-Scale Skeletal Banding Can Distinguish Symbiotic from Asymbiotic Species among Modern and Fossil Scleractinian Corals. PLoS ONE, 2016, 11, e0147066.	1.1	25
23	Homogenous indium distribution in InGa _N /Ga _N laser active structure grown by LP-MOCVD on bulk Ga _N crystal revealed by transmission electron microscopy and x-ray diffraction. Nanotechnology, 2007, 18, 465707.	1.3	23
24	Quantitative Strain Mapping Applied to Aberration-Corrected HAADF Images. Microscopy and Microanalysis, 2006, 12, 285-294.	0.2	22
25	UV-excited piezo-optical effects in oxide nanocrystals incorporated into PMMA matrices. Acta Materialia, 2008, 56, 5677-5684.	3.8	22
26	Atomic-scale mapping of local lattice distortions in highly strained coherent islands of In _x Ga _{1-x} As/GaAs by high-resolution electron microscopy and image processing. Philosophical Magazine Letters, 1998, 77, 249-256.	0.5	21
27	On the measurement of dislocation core distributions in a GaAs/ZnTe/CdTe heterostructure by high-resolution transmission electron microscopy. Philosophical Magazine, 2003, 83, 231-244.	0.7	21
28	Mechanism of formation of the misfit dislocations at the cubic materials interfaces. Applied Physics Letters, 2012, 100, .	1.5	21
29	Growth mechanisms in semipolar $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0020.gif" overflow="scroll" \rangle \langle \text{mml:mo stretchy="false" \rangle} \langle \text{mml:mn} \rangle 2 \langle \text{mml:mn} \rangle \langle \text{mml:mspace width=".5em"} \rangle \text{Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 347 Te}$	0.7	20
30	Measurement of dislocation core distribution by digital processing of high-resolution transmission electron microscopy micrographs: a new technique for studying defects. Journal of Physics Condensed Matter, 2000, 12, 10313-10318.	0.7	19
31	Zn _{1-x} Mn _x Te Diluted Magnetic Semiconductor Nanowires Grown by Molecular Beam Epitaxy. Nano Letters, 2008, 8, 4061-4065.	4.5	19
32	Growth mode transition and relaxation of thin InGa _N layers on Ga _N (0001). Journal of Crystal Growth, 2013, 372, 65-72.	0.7	19
33	Self-organized MnAs quantum dots formed during annealing of GaMnAs under arsenic capping. Applied Physics Letters, 2005, 87, 263114.	1.5	18
34	The source of the threading dislocation in GaSb/GaAs hetero-structures and their propagation mechanism. Applied Physics Letters, 2013, 102, 052102.	1.5	17
35	Magneto-transport in inverted HgTe quantum wells. Npj Quantum Materials, 2019, 4, .	1.8	16
36	TEM characterization of VLS-grown ZnTe nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3780-3784.	0.8	15

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37	Wurtzite (Ga,Mn)As nanowire shells with ferromagnetic properties. <i>Nanoscale</i> , 2017, 9, 2129-2137.	2.8	15
38	Role of Metal Vacancies in the Mechanism of Thermal Degradation of InGaN Quantum Wells. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 7476-7484.	4.0	15
39	Magnetic properties of MnSb inclusions formed in GaSb matrix directly during molecular beam epitaxial growth. <i>Journal of Applied Physics</i> , 2011, 109, 074308.	1.1	14
40	Investigation of the In composition in InGaN/GaN quantum wells deposited by MOVPE and/or MBE with emission from violet to green. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1187-1190.	0.7	14
41	Growth and optical properties of CdTe quantum dots in ZnTe nanowires. <i>Applied Physics Letters</i> , 2011, 99, 113109.	1.5	14
42	Thermal annealing of molecular beam epitaxy-grown InGaN/GaN single quantum well. <i>Semiconductor Science and Technology</i> , 2012, 27, 105023.	1.0	14
43	Enhanced Ferromagnetism in Cylindrically Confined MnAs Nanocrystals Embedded in Wurtzite GaAs Nanowire Shells. <i>Nano Letters</i> , 2019, 19, 7324-7333.	4.5	14
44	The effect of local atomic structure on the optical properties of GeSi self-assembled islands buried in silicon matrix. <i>Nanotechnology</i> , 2007, 18, 115711.	1.3	13
45	Activation of an intense near band edge emission from ZnTe/ZnMgTe core/shell nanowires grown on silicon. <i>Nanotechnology</i> , 2013, 24, 365201.	1.3	13
46	Strain-induced energy gap variation in ZnTe/ZnMgTe core/shell nanowires. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	13
47	Experimental search for the origin of low-energy modes in topological materials. <i>Physical Review B</i> , 2019, 100, .	1.1	12
48	Compositional and strain analysis of In(Ga)N/GaN short period superlattices. <i>Journal of Applied Physics</i> , 2018, 123, 024304.	1.1	11
49	Analysis of strain in the {112},0} prismatic fault in GaN using digital processing of high-resolution transmission electron microscopy images. <i>Journal of Physics Condensed Matter</i> , 2000, 12, 10249-10256.	0.7	10
50	The dislocations of low-angle grain boundaries in GaN epilayers: a HRTEM quantitative study and finite element stress state calculation. <i>Diamond and Related Materials</i> , 2002, 11, 910-913.	1.8	10
51	Inhomogeneities of InGaN/GaN MOVPE multi quantum wells grown with a two temperatures process studied by transmission electron microscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 1101-1104.	0.8	10
52	Investigation of the anisotropic strain relaxation in GaSb islands on GaP. <i>Journal of Applied Physics</i> , 2011, 110, 043509.	1.1	10
53	TEM and XANES study of MOVPE grown InAlN layers with different indium content. <i>Journal of Physics: Conference Series</i> , 2011, 326, 012013.	0.3	10
54	Evidence of relationship between strain and In-incorporation: Growth of N-polar In-rich InAlN buffer layer by OMCVD. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	10

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55	Room temperature infrared detectors made of PbTe/CdTe multilayer composite. Applied Physics Letters, 2020, 117, 072102.	1.5	10
56	Zn _{1-x} Mg _x Te nanowires grown by solid source molecular beam epitaxy. Nanotechnology, 2008, 19, 365606.	1.3	9
57	Structural and magnetic properties of the molecular beam epitaxy grown MnSb layers on GaAs substrates. Journal of Applied Physics, 2009, 106, .	1.1	9
58	Influence of the Si cap layer on the SiGe islands morphology. Micron, 2009, 40, 122-125.	1.1	9
59	Antimony-Mediated Control of Misfit Dislocations and Strain at the Highly Lattice Mismatched GaSb/GaAs Interface. ACS Applied Materials & Interfaces, 2013, 5, 9760-9764.	4.0	9
60	Nanoscale morphology of multilayer PbTe/CdTe heterostructures and its effect on photoluminescence properties. Nanotechnology, 2015, 26, 135601.	1.3	9
61	Self-organization process in crystalline PbTe/CdTe multilayer structures: Experiment and Monte Carlo simulations. Journal of Alloys and Compounds, 2018, 747, 809-814.	2.8	9
62	Defect-free SnTe topological crystalline insulator nanowires grown by molecular beam epitaxy on graphene. Nanoscale, 2018, 10, 20772-20778.	2.8	9
63	Role of Substrate Misorientation in Relaxation of 3C-SiC Layers on Silicon. Materials Science Forum, 0, 615-617, 169-172.	0.3	8
64	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metal-Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	0.8	8
65	Growth and optical properties of ZnO/Zn _x Mg _x O quantum wells on ZnO microrods. Nanoscale, 2019, 11, 2275-2281.	2.8	8
66	Charge transport in MBE-grown 2H-MoTe ₂ bilayers with enhanced stability provided by an AlO _x capping layer. Nanoscale, 2020, 12, 16535-16542.	2.8	8
67	Molecular Beam Epitaxy of a 2D Material Nearly Lattice Matched to a 3D Substrate: NiTe ₂ on GaAs. Crystal Growth and Design, 2021, 21, 5773-5779.	1.4	8
68	TEM characterization of MBE grown CdTe/ZnTe axial nanowires. Journal of Microscopy, 2010, 237, 337-340.	0.8	7
69	Synthesis and magneto-optic characterization of Cu-doped ZnO/MgO and ZnO/oleic acid core/shell nanoparticles. RSC Advances, 2016, 6, 44820-44825.	1.7	7
70	Coexistence of optically active radial and axial CdTe insertions in single ZnTe nanowire. Nanoscale, 2016, 8, 5720-5727.	2.8	7
71	Nanometric Scale Investigation of Local Strain in GaInAs Islands by High Resolution and Analytical TEM. Microscopy and Microanalysis, 2002, 8, 312-318.	0.2	6
72	TEM determination of directions of (Ga,Mn)As nanowires grown by MBE on GaAs(001) substrates. Journal of Microscopy, 2009, 236, 115-118.	0.8	6

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73	Growth and optical investigations of high quality individual CdTe/(Cd,Mg)Te core/shell nanowires. Nanotechnology, 2017, 28, 045207.	1.3	6
74	Magnetic field induced mixing of light hole excitonic states in (Cd, Mn)Te/(Cd, Mg)Te core/shell nanowires. Nanotechnology, 2018, 29, 205205.	1.3	6
75	Digital Magnetic Quantum Wells for the Study of Interface Sharpness of Molecular Beam Epitaxy Grown Structures. Acta Physica Polonica A, 1995, 87, 165-168.	0.2	6
76	Quantitative measurement of In fluctuation inside MOCVD InGaN QWs. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 185-188.	1.7	5
77	Quantitative evaluation of the atomic structure of defects and composition fluctuations at the nanometer scale inside InGaN/GaN heterostructures. Physica Status Solidi (B): Basic Research, 2004, 241, 2735-2738.	0.7	5
78	Piezoelectric field around threading dislocation in GaN determined on the basis of high-resolution transmission electron microscopy image. Journal of Microscopy, 2006, 223, 212-215.	0.8	5
79	Observation of Asymmetric Wafer Bending for 3C-SiC Thin Films Grown on Misoriented Silicon Substrates. Materials Research Society Symposia Proceedings, 2008, 1069, 1.	0.1	5
80	TEM analysis of the container effect of Au-based catalyst droplets during vapour-liquid-solid growth of axial ZnTe/CdTe nanowires. Crystal Research and Technology, 2009, 44, 1047-1053.	0.6	5
81	Capture kinetics at deep-level defects in MBE-grown CdTe layers. Semiconductor Science and Technology, 2011, 26, 045008.	1.0	5
82	Structural and magnetic properties of GaSb:MnSb granular layers. Radiation Physics and Chemistry, 2011, 80, 1051-1057.	1.4	5
83	The critical role of N-vacancy on chemical composition fluctuations and degradation of InAlN layer. Journal of Applied Physics, 2019, 125, 215707.	1.1	5
84	Photoluminescence Properties of ZnO and ZnCdO Nanowires. Acta Physica Polonica A, 2007, 112, 357-362.	0.2	5
85	Strain Relaxation of ZnTe/CdTe and CdTe/ZnTe heterostructures: In Situ Study. Acta Physica Polonica A, 1996, 90, 911-914.	0.2	5
86	Polarization and magneto-optical properties of excitonic emission from wurtzite CdTe/(Cd,Mg)Te core/shell nanowires. Nanotechnology, 2020, 31, 215710.	1.3	4
87	Phase-transition critical thickness of rocksalt Mg _x Zn _{1-x} O layers. Journal of Chemical Physics, 2021, 154, 154701.	1.2	4
88	Nanostructure of Si-Ge Near-Surface Layers Produced by Ion Implantation and Laser Annealing. Acta Physica Polonica A, 2002, 102, 259-264.	0.2	4
89	Growth and Properties of ZnMnTe Nanowires. Acta Physica Polonica A, 2007, 112, 351-356.	0.2	4
90	TEM Study of the Structural Properties of Nanowires Based on Cd, Zn, Te grown by MBE on Silicon Substrates. Acta Physica Polonica A, 2017, 131, 1399-1405.	0.2	4

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91	ZnSe/CdSe Superlattice Nanowires by Catalyst-assisted Molecular Beam Epitaxy. AIP Conference Proceedings, 2007, , .	0.3	3
92	Three-dimensional localization of excitons in the InAs/GaAs wetting layer – magnetospectroscopic study. Physica Status Solidi (B): Basic Research, 2009, 246, 850-853.	0.7	3
93	Laser-deposited Cu/Al ₂ O ₃ nanocomposite: experiment and modeling. Applied Physics A: Materials Science and Processing, 2014, 117, 169-173.	1.1	3
94	Influence of substrate temperature on incorporation of magnesium into Zn _{1-x} Mg _x O layers growth by molecular beam epitaxy. Journal of Alloys and Compounds, 2018, 766, 398-401.	2.8	3
95	Structural defects in MBE-grown CdTe-basing heterojunctions designed for photovoltaic applications. Semiconductor Science and Technology, 2021, 36, 045022.	1.0	3
96	Neutral and Charged Excitons Localized in the InAs/GaAs Wetting Layer. Acta Physica Polonica A, 2008, 114, 1055-1060.	0.2	3
97	Morphology and Selected Properties of Core/Shell ZnTe-Based Nanowire Structures Containing ZnO. Acta Physica Polonica A, 2011, 119, 612-614.	0.2	3
98	Influence of Growth Polarity Switching on the Optical and Electrical Properties of GaN/AlGaIn Nanowire LEDs. Electronics (Switzerland), 2021, 10, 45.	1.8	3
99	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metal-Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	0.8	3
100	Finite Element Simulation of Residual Stresses in Epitaxial Layers. Materials Science Forum, 2002, 404-407, 141-146.	0.3	2
101	Contribution to quantitative measurement of the In composition in GaN/InGaIn multilayers. Materials Chemistry and Physics, 2003, 81, 273-276.	2.0	2
102	A transmission electron microscopy study of composition in Si _{1-x} Gex/Si (001) quantum dots. Philosophical Magazine, 2007, 87, 1531-1543.	0.7	2
103	TEM investigation of a processed InGaIn based laser grown by PAMBE on bulk GaIn substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1325-1328.	0.8	2
104	Zn _{1-x} Mn _x Te-based diluted magnetic semiconductor nanowire structures grown by MBE. , 2010, , .		2
105	(Zn,Mn)Te-Based Nanowires for Spintronic Applications: A TEM Study of Structural and Chemical Properties. Materials Science Forum, 2010, 638-642, 2154-2159.	0.3	2
106	Low loss EEL spectroscopy performed on In _x Al _{1-x} N layers grown by MOVPE: comparison between experiment and ab-initio calculations. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 989-992.	0.8	2
107	Extended defects in MBE-grown CdTe-based solar cells. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1115-1118.	0.8	2
108	Engineering the hole confinement for CdTe-based quantum dot molecules. Journal of Applied Physics, 2015, 117, .	1.1	2

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109	Oxidation of MBE-Grown ZnTe and ZnTe/Zn Nanowires and Their Structural Properties. <i>Materials</i> , 2021, 14, 5252.	1.3	2
110	Role of high nitrogen flux in InAlN growth by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2020, 544, 125720.	0.7	2
111	FIB Method of Sectioning of III-V Core-Multi-Shell Nanowires for Analysis of Core/Shell Interfaces by High Resolution TEM. <i>Acta Physica Polonica A</i> , 2017, 131, 1332-1336.	0.2	2
112	Off-Axis Electron Holography of Magnetic Nanostructures: Magnetic Behavior of Mn Rich Nanoprecipitates in (Mn,Ga)As System. <i>Acta Physica Polonica A</i> , 2017, 131, 1406-1409.	0.2	2
113	Lattice Parameter Relaxation during MBE of ZnTe/Cd _{1-x} Zn _x Te/Cd _{0.5} Zn _{0.5} Te Buffer Layers by RHLED and HRTEM. <i>Acta Physica Polonica A</i> , 1995, 88, 795-798.	0.2	2
114	Analysis of strain in sub-grains with variable misorientation in GaN epilayers by digital processing of HRTEM images. <i>Materials Research Society Symposia Proceedings</i> , 2000, 639, 11541.	0.1	1
115	Three-Dimensional Quantum Dot ?Crystal? Formation in CdTe/ZnTe Superlattices. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 445-448.	0.7	1
116	Investigation of the InGaN Quantum Wells Compositional Inhomogeneity. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 307-310.	0.8	1
117	Structure of Magnetically Ordered Si:Mn. <i>Solid State Phenomena</i> , 2007, 131-133, 327-332.	0.3	1
118	Atomic order in magnetic Mn inclusions in Si crystals: XAS and TEM studies. <i>Journal of Non-Crystalline Solids</i> , 2008, 354, 4189-4192.	1.5	1
119	Effects of the annealing temperature on the structural and electronic properties of MBE grown InGaN/GaN quantum wells. <i>Journal of Physics: Conference Series</i> , 2011, 326, 012012.	0.3	1
120	Surface morphology created by nanosecond laser annealing of amorphised Si layer – Investigations by complementary methods. <i>Radiation Physics and Chemistry</i> , 2011, 80, 1031-1035.	1.4	1
121	Strong s ^d exchange coupling in ZnMnTe/ZnMgTe core/shell nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1308-1311.	0.8	1
122	Near-infrared emission from spatially indirect excitons in type II ZnTe/CdSe/(Zn,Mg)Te core/double-shell nanowires. <i>Nanotechnology</i> , 2021, 32, 495202.	1.3	1
123	Structural and Chemical Properties of ZnTe Nanowires Grown on GaAs. <i>Springer Proceedings in Physics</i> , 2008, , 233-236.	0.1	1
124	Impact of Thin LT-GaN Cap Layers on the Structural and Compositional Quality of MOVPE Grown InGaN Quantum Wells Investigated by TEM. <i>Acta Physica Polonica A</i> , 2011, 119, 660-662.	0.2	1
125	In Situ Electron Beam Amorphization of Sb ₂ Te ₃ within Single Walled Carbon Nanotubes. <i>Acta Physica Polonica A</i> , 2017, 131, 1324-1328.	0.2	1
126	Application of Graphics Processing Unit for In-Line Electron Holography. <i>Acta Physica Polonica A</i> , 2017, 131, 1353-1357.	0.2	1

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127	Magneto-optical Properties of Graded Quantum Well Structures Made of Diluted Magnetic Semiconductors. , 2000, , 237-246.		1
128	Quantitative measurements of the inhomogeneous strain field of stacked self-assembled InAs/InP(001) quantum wires by the Peak Finding Method. , 0, , 299-302.		1
129	Precise strain mapping of nano-twinned axial ZnTe/CdTe hetero-nanowires by scanning nanobeam electron diffraction. Nanotechnology, 2022, 33, 195704.	1.3	1
130	Bi incorporation and segregation in the MBE-grown GaAs-(Ga,Al)As-Ga(As,Bi) core-shell nanowires. Scientific Reports, 2022, 12, 6007.	1.6	1
131	Local Stress in Highly Strained Coherent InGaAs Islands. Materials Science Forum, 1999, 294-296, 649-652.	0.3	0
132	Indium distribution inside quantum wells: The effect of growth interruption in MBE. Materials Research Society Symposia Proceedings, 2002, 743, L6.6.1.	0.1	0
133	Evidence of strong indium segregation in MOCVD In _x Ga _{1-x} N/GaN quantum layers. Materials Research Society Symposia Proceedings, 2003, 798, 176.	0.1	0
134	Modelling of indium rich clusters in MOCVD In _{1-x} Ga _x N/GaN multilayers. Journal of Alloys and Compounds, 2004, 382, 10-16.	2.8	0
135	Size and shape of In rich clusters and InGaN QWs at the nanometer scale. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2381-2384.	0.8	0
136	Strain, Chemical Composition, and Defects Analysis at Atomic Level in GaN-based Epitaxial Layers. , 2006, , 439-488.		0
137	CdTe Quantum Dots in a Field Effect Structure: Photoluminescence Lineshape Analysis. , 2010, , .		0
138	Structural characterization of the epitaxially grown core-shell ZnTe/ZnMgTe nanowires. Radiation Physics and Chemistry, 2013, 93, 111-116.	1.4	0
139	ZnTe nanowires grown catalytically on GaAs (001) substrates by molecular beam epitaxy. AIP Conference Proceedings, 2007, , .	0.3	0
140	Analysis of atomic structure and structural imperfections of ZnTe and (Zn,Mn)Te nanowires. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C598-C598.	0.3	0
141	Indium rich clusters in MOCVD InGaN/GaN: high resolution electron microscopy study and finite element modelling. , 2018, , 61-64.		0
142	Chemical composition and strain distribution of InAs/GaAs(001) stacked quantum rings. , 0, , 271-274.		0
143	TEM analysis of the chemical gradient in (Zn,Mn)Te/ZnTe nanowires. , 2008, , 301-302.		0